

Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 0.1~0.8GHz
- Typical Pout : $\geq 43\text{dBm(CW)}$
- Typical Gain: $\geq 14\text{dB}$
- Typical PAE: $\geq 55\%$
- Bias: 28V/-2.6~-1.6V@0.3A
- Package: Metal Ceramic

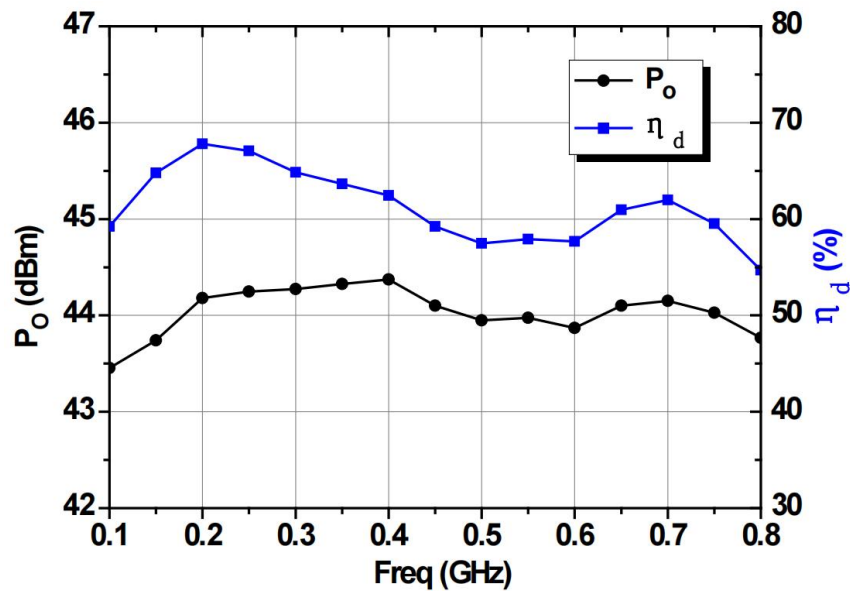


Electrical Specifications ($T_A=25^\circ\text{C}$, $V_d=28\text{V}$, $I_{dq}=0.3\text{A}$, $P_{in}=29\text{dBm}$, $F: 0.1\sim 0.8\text{GHz}$)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	43	-	-	dBm
Gp	Power Gain	14	-	-	dB
η_{add}	Power Added Efficiency	55	-	-	%
ΔGp	Gain Flatness	-	-	± 0.5	dB

Test Curves

Pout/PAE&Freq.

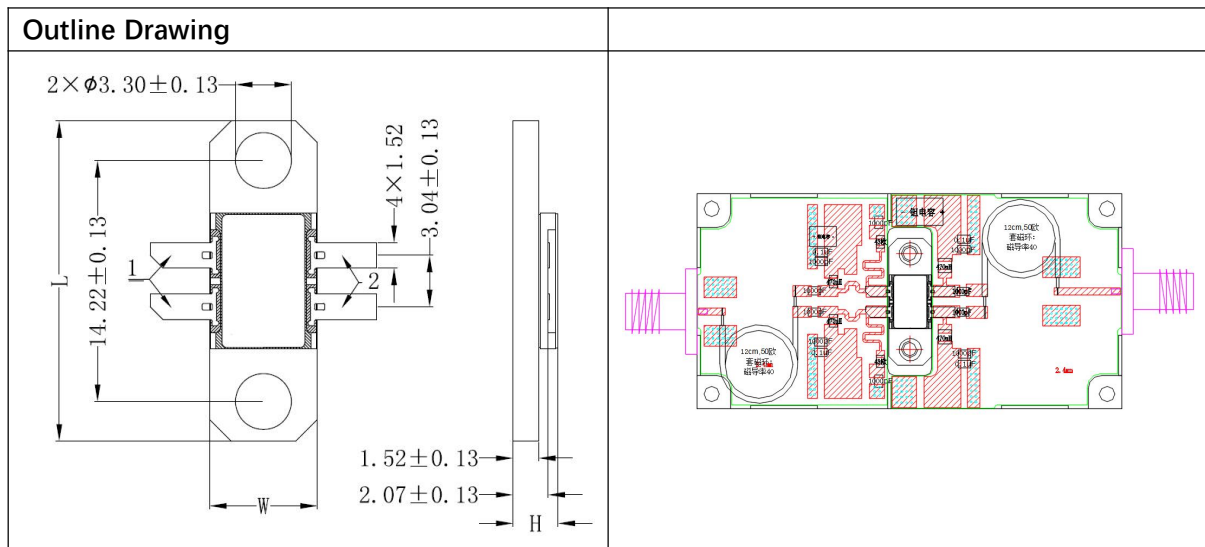


Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
V _d	Drain Voltage	36V	
V _g	Grid Voltage	-5V	
P _d	DC Dissipation	80W	25°C
T _{ch}	Channel Temperature	225°C	【1】
T _m	Mounting Temperature	300°C	1 min, N ₂ Protection
T _{stg}	Storage Temperature	-55~150°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing



Note:

- (1) Please strictly follow the order of adding negative electricity first and then positive electricity in the power-on sequence of this product. When de-energizing, first reduce the drain voltage and then reduce the gate voltage;
- (2) Pay attention to heat dissipation during the use of this product. The higher the shell temperature, the shorter the service life, and the operating temperature should not be higher than 85 degrees;
- (3) This product is an electrostatic sensitive device, you need to pay attention to electrostatic protection during storage and use, and you need to be well grounded when using it;
- (4) The input standing wave is relatively high, and isolation measures are required at the input end.